
2SB647, 2SB647A

Silicon PNP Epitaxial

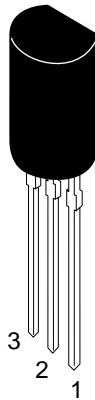
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Application

- Low frequency power amplifier
- Complementary pair with 2SD667/A

Outline

TO-92MOD



1. Emitter
2. Collector
3. Base

2SB647, 2SB647A

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	2SB647	2SB647A	Unit
Collector to base voltage	V_{CBO}	-120	-120	V
Collector to emitter voltage	V_{CEO}	-80	-100	V
Emitter to base voltage	V_{EBO}	-5	-5	V
Collector current	I_C	-1	-1	A
Collector peak current	$i_{C(peak)}$	-2	-2	A
Collector power dissipation	P_C	0.9	0.9	W
Junction temperature	T_j	150	150	°C
Storage temperature	T_{stg}	-55 to +150	-55 to +150	°C

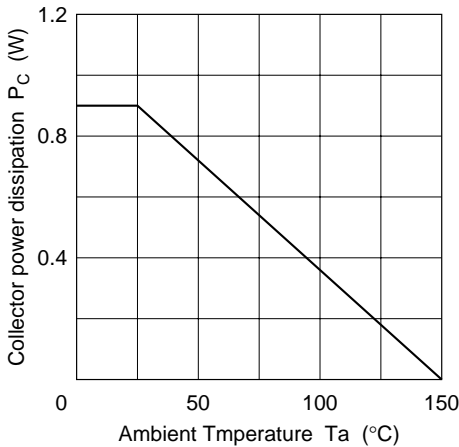
Electrical Characteristics (Ta = 25°C)

Item	Symbol	2SB647			2SB647A			Unit	Test conditions
		Min	Typ	Max	Min	Typ	Max		
Collector to base breakdown voltage	$V_{(BR)CBO}$	-120	—	—	-120	—	—	V	$I_C = -10\text{ }\mu\text{A}$, $I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-80	—	—	-100	—	—	V	$I_C = -1\text{ mA}$, $R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-5	—	—	-5	—	—	V	$I_E = -10\text{ }\mu\text{A}$, $I_C = 0$
Collector cutoff current	I_{CBO}	—	—	-10	—	—	-10	μA	$V_{CB} = -100\text{ V}$, $I_E = 0$
DC current transfer ratio	h_{FE1}^{*1}	60	—	320	60	—	200		$V_{CE} = -5\text{ V}$, $I_C = -150\text{ mA}^{*2}$
	h_{FE2}	30	—	—	30	—	—		$V_{CE} = -5\text{ V}$, $I_C = -500\text{ mA}^{*2}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	-1	—	—	-1	V	$I_C = -500\text{ mA}$, $I_B = -50\text{ mA}^{*2}$
Base to emitter voltage	V_{BE}	—	—	-1.5	—	—	-1.5	V	$V_{CE} = -5\text{ V}$, $I_C = -150\text{ mA}^{*2}$
Gain bandwidth product	f_T	—	140	—	—	140	—	MHz	$V_{CE} = -5\text{ V}$, $I_C = -150\text{ mA}$
Collector output capacitance	C_{ob}	—	20	—	—	20	—	pF	$V_{CB} = -10\text{ V}$, $I_E = 0$ $f = 1\text{ MHz}$

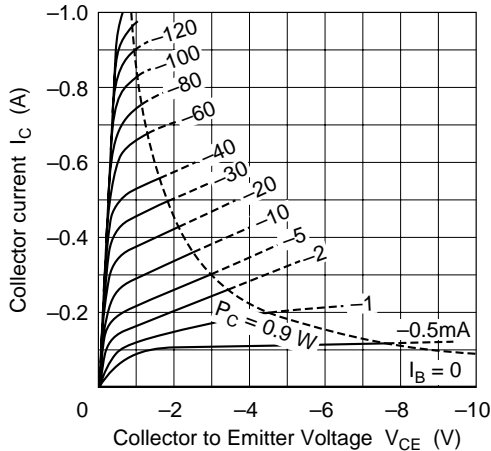
Notes: 1. The 2SB647 and 2SB647A are grouped by h_{FE1} as follows.
2. Pulse test

	B	C	D
2SB647	60 to 120	100 to 200	160 to 320
2SB647A	60 to 120	100 to 200	—

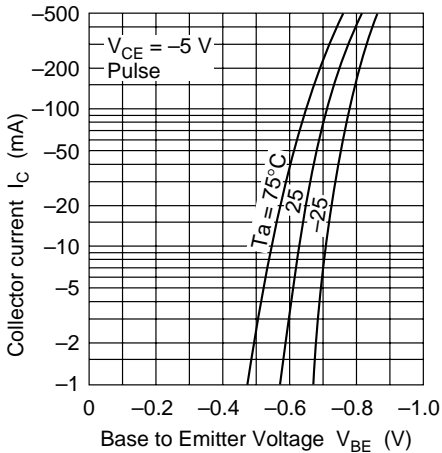
Maximum Collector Dissipation Curve



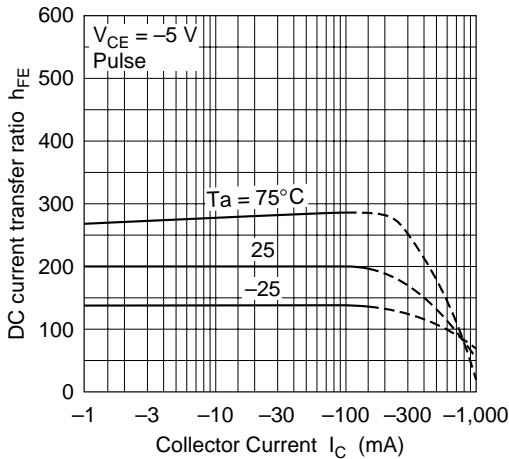
Typical Output Characteristics



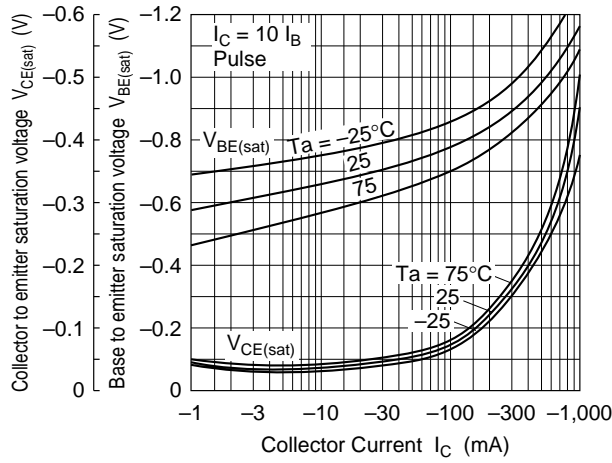
Typical Transfer Characteristics



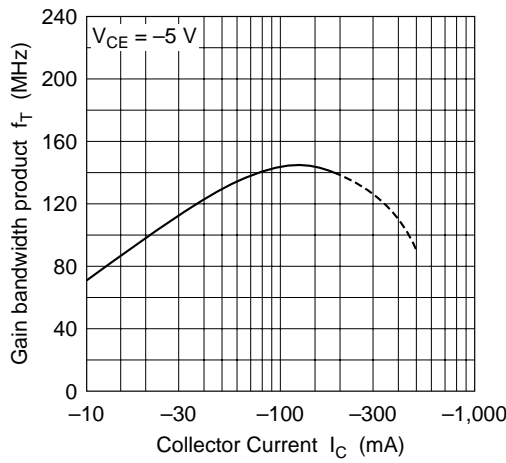
DC Current Transfer Ratio vs. Collector Current



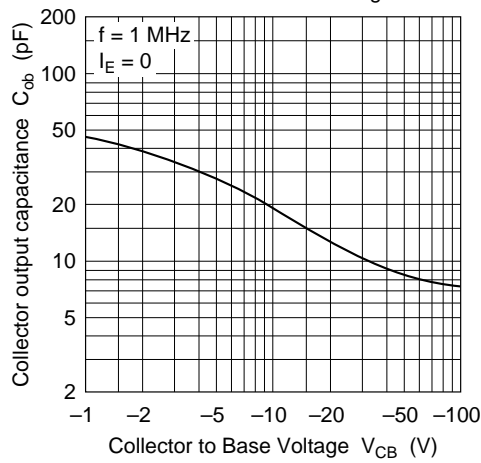
Saturation Voltage
vs. Collector Current

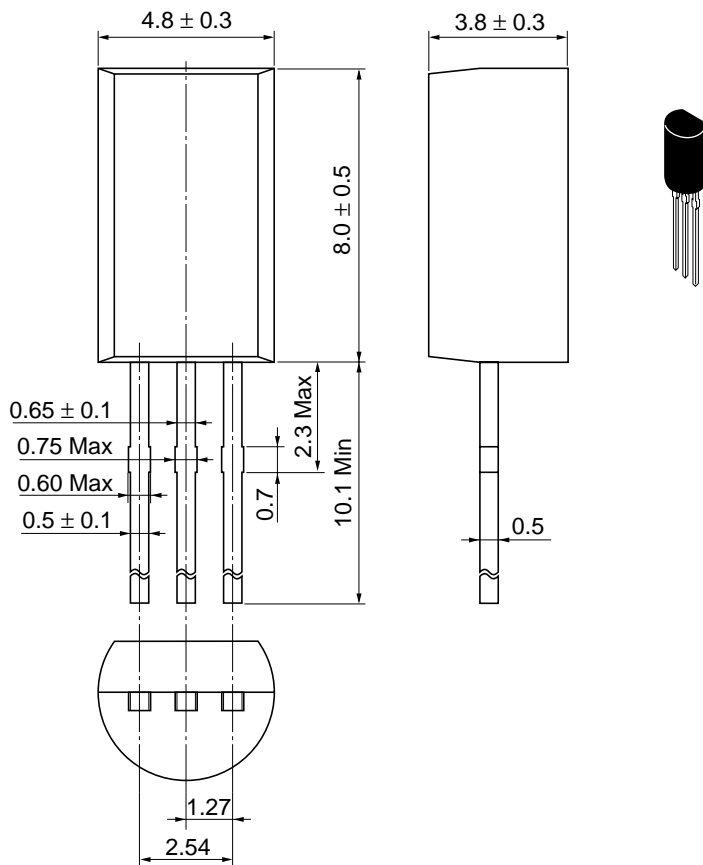


Gain Bandwidth Product
vs. Collector Current



Collector Output Capacitance vs.
Collector to Base Voltage





Hitachi Code	TO-92 Mod
JEDEC	—
EIAJ	Conforms
Weight (reference value)	0.35 g

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Hitachi, Ltd.

Semiconductor & Integrated Circuits.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

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For further information write to:

Hitachi Semiconductor (America) Inc. 179 East Tasman Drive, San Jose, CA 95134 Tel: <1> (408) 433-1990 Fax: <1> (408) 433-0223	Hitachi Europe GmbH Electronic components Group Dornacher Straße 3 D-85622 Feldkirchen, Munich Germany Tel: <49> (89) 9 9180-0 Fax: <49> (89) 9 29 30 00 Hitachi Europe Ltd. Electronic Components Group. Whitebrook Park Lower Cookham Road Maidenhead Berkshire SL6 8YA, United Kingdom Tel: <44> (1628) 585000 Fax: <44> (1628) 778322
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Hitachi Asia Pte. Ltd.
16 Collyer Quay #20-00
Hitachi Tower
Singapore 049318
Tel: 535-2100
Fax: 535-1533

Hitachi Asia Ltd.
Taipei Branch Office
3F, Hung Kuo Building, No.167,
Tun-Hwa North Road, Taipei (105)
Tel: <886> (2) 2718-3666
Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower, World Finance Centre,
Harbour City, Canton Road, Tsim Sha Tsui,
Kowloon, Hong Kong
Tel: <852> (2) 735 9218
Fax: <852> (2) 730 0281
Telex: 40815 HITEC HX

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